

ERRATUM

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Erratum to: Strong Pinned-Spin-Mediated Memory Effect in NiO Nanoparticles

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Erratum

In the original publication [1] was an error in the authors contribution. The correct version can be found here:

“SYW and ACG wrote, conceived, and designed the experiments. ACG and JP grew the samples and analyzed the data. TSC and JP contributed the experimental facilities and valuable discussions. All authors discussed the results, contributed to the manuscript text, commented on the manuscript, and approved its final version.”

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Received: 19 April 2017 Accepted: 19 April 2017

Published online: 05 May 2017

Reference

1. (2017) Strong Pinned-Spin-Mediated Memory Effect in NiO Nanoparticles. *Nanoscale Res Lett* 12:207. doi:10.1186/s11671-017-1988-x

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